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producing a semiconductor device. More particularly, the present invention relates to a method of fabricating a semiconductor device in which a flow of ions is prevented from being generated. 2. Description of the Related Art In the fabrication of a semiconductor device, for example, a gate insulating layer is conventionally formed on a semiconductor substrate by thermal oxidation. However, to form the gate insulating layer by thermal oxidation, it is generally necessary to apply a prebaking step to a wafer in an oxygen atmosphere, such as an oxidation atmosphere or a wet oxidation atmosphere. As a result, oxygen ions and/or water molecules are generated, which may form a flow of ions along the boundary between the semiconductor substrate and the gate insulating layer. For example, when a gate insulating layer is formed on an n-type semiconductor substrate made of silicon, oxygen ions are generated during a prebaking step in a wet oxidation atmosphere. These oxygen ions are then allowed to flow along the

boundary between the gate insulating layer and the semiconductor substrate. When a flow of ions is generated, the surface of the semiconductor substrate is roughened due to mutual diffusion between the semiconductor substrate and the gate insulating layer. As a result, the surface of the semiconductor substrate is roughened and thus the gate insulating layer and a device such as a MOSFET may be degraded.

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